

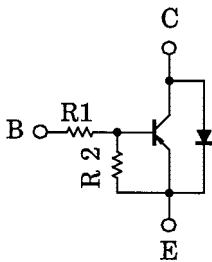
TENTATIVE TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2357

Driver Circuit, Inverter Circuit, and Switching Applications

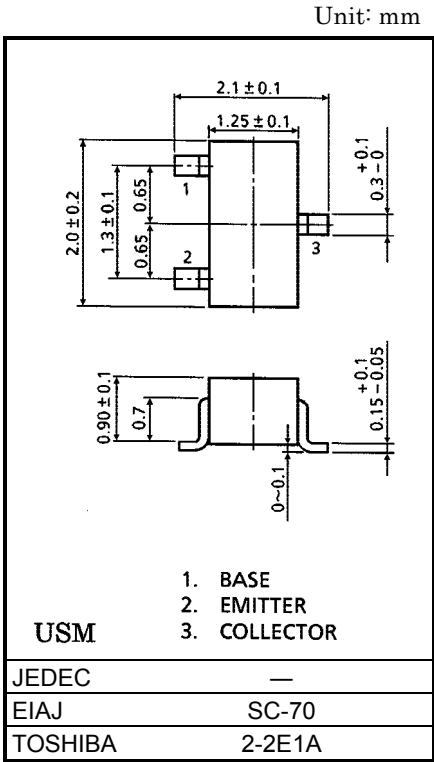
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- RN2307 and a diode are included in a SC-70 package.

Equivalent Circuit (Top View)



Bias Resistor Values

R1 (kΩ)	R2 (kΩ)
10	47



Maximum Ratings (Ta = 25°C)

Characterisctic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	−50	V
Collector-emitter voltage	V _{CEO}	−50	V
Emitter-base voltage	V _{EBO}	−6	V
Collector current	I _C	−100	mA
Collector power dissipation	P _C	100	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	−55~150	°C

Marking

